

	Type	L #	Hits	Search Text	DBs
1	BRS	L1	3872	"438"/\$.ccls. and (interposer substrate carrier) same (conductive metal) adj2 (film layer material) same mask same pattern\$3	USPAT; EPO; JPO; DERWEN T; IBM_TD B
2	BRS	L2	1789	l1 and mask with (openings hole via)	USPAT; EPO; JPO; DERWEN T; IBM_TD B
3	BRS	L4	101	l1 and mask with (openings hole via) and trace	USPAT; EPO; JPO; DERWEN T; IBM_TD B
4	BRS	L5	80	438/612 and (interposer substrate carrier) same (conductive metal) adj2 (film layer material) same mask same pattern\$3	USPAT; EPO; JPO; DERWEN T; IBM_TD B
5	BRS	L6	74	438/612 and (interposer substrate carrier) same (conductive metal) adj2 (film layer material) same mask same pattern\$3 and (electrode pad terminal)	USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
6	BRS	L8	71	438/613 and (interposer substrate carrier) same (conductive metal) adj2 (film layer material) same mask same pattern\$3 and (electrode pad terminal)	USPAT; EPO; JPO; DERWEN T; IBM_TD B
7	BRS	L9	56	438/614 and (interposer substrate carrier) same (conductive metal) adj2 (film layer material) same mask same pattern\$3 and (electrode pad terminal)	USPAT; EPO; JPO; DERWEN T; IBM_TD B
8	BRS	L10	87	438/614 and (interposer substrate carrier) same (conductive metal) adj2 (film layer material) same (photoresist mask) same pattern\$3 and (electrode pad terminal)	USPAT; EPO; JPO; DERWEN T; IBM_TD B
9	BRS	L11	105	438/612 and (interposer substrate carrier) same (conductive metal) adj2 (film layer material) same (photoresist mask) same pattern\$3 and (electrode pad terminal)	USPAT; EPO; JPO; DERWEN T; IBM_TD B
10	BRS	L12	21	438/110 and (interposer substrate carrier) same (conductive metal) adj2 (film layer material) same (photoresist mask) same pattern\$3 and (electrode pad terminal)	USPAT; EPO; JPO; DERWEN T; IBM_TD B

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11	BRS	L13	288	438/637 and (interposer substrate carrier) same (conductive metal) adj2 (film layer material) same (photoresist mask) same pattern\$3 and (electrode pad terminal)	USPAT; EPO; JPO; DERWEN T; IBM_TD B
12	BRS	L14	47	438/125 and (interposer substrate carrier) same (conductive metal) adj2 (film layer material) same (photoresist mask) same pattern\$3 and (electrode pad terminal)	USPAT; EPO; JPO; DERWEN T; IBM_TD B
13	BRS	L15	6	("20010002321"   "5341564"   "5420460"   "5578261"   "5639695"   "5796586").PN.	US- PGPUB; USPAT; USOCR
14	BRS	L16	82	438/638 and (interposer substrate carrier) same (conductive metal) adj2 (film layer material) same (photoresist mask) same pattern\$3 and (electrode pad terminal)	USPAT; EPO; JPO; DERWEN T; IBM_TD B
15	BRS	L17	53	438/652 and (interposer substrate carrier) same (conductive metal) adj2 (film layer material) same (photoresist mask) same pattern\$3 and (electrode pad terminal)	USPAT; EPO; JPO; DERWEN T; IBM_TD B
16	BRS	L18	132	438/669 and (interposer substrate carrier) same (conductive metal) adj2 (film layer material) same (photoresist mask) same pattern\$3 and (electrode pad terminal)	USPAT; EPO; JPO; DERWEN T; IBM_TD B

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17	BRS	L19	423	"438"/\$.ccls. and interposer	USPAT; EPO; JPO; DERWEN T; IBM_TD B
18	BRS	L20	132	257/773 and (interposer substrate carrier) same (conductive metal) adj2 (film layer material) same (photoresist mask) same pattern\$3 and (electrode pad terminal)	USPAT; EPO; JPO; DERWEN T; IBM_TD B
19	BRS	L21	60	257/786 and (interposer substrate carrier) same (conductive metal) adj2 (film layer material) same (photoresist mask) same pattern\$3 and (electrode pad terminal)	USPAT; EPO; JPO; DERWEN T; IBM_TD B
20	BRS	L22	1225	"257"/\$.ccls. and interposer	USPAT; EPO; JPO; DERWEN T; IBM_TD B
21	BRS	L23	55	257/786 and interposer and (photoresist mask) and (electrode pad terminal)	USPAT; EPO; JPO; DERWEN T; IBM_TD B

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22	BRS	L24	112	257/786 and interposer and (photoresist mask pattern\$3) and (electrode pad terminal)	USPAT; EPO; JPO; DERWEN T; IBM_TD B
23	BRS	L25	19	29/829 and (interposer substrate carrier) same (conductive metal) adj2 (film layer material) same (photoresist mask) same pattern\$3 and (electrode pad terminal)	USPAT; EPO; JPO; DERWEN T; IBM_TD B
24	BRS	L26	121	29/846 and (interposer substrate carrier) same (conductive metal) adj2 (film layer material) same (photoresist mask) same pattern\$3 and (electrode pad terminal)	USPAT; EPO; JPO; DERWEN T; IBM_TD B
25	BRS	L27	3	("6265301"   "6383401"   "6684497").PN.	US- PGPUB; USPAT; USOCR
26	BRS	L28	45	29/847 and (interposer substrate carrier) same (conductive metal) adj2 (film layer material) same (photoresist mask) same pattern\$3 and (electrode pad terminal)	USPAT; EPO; JPO; DERWEN T; IBM_TD B
27	BRS	L29	5	29/849 and (interposer substrate carrier) same (conductive metal) adj2 (film layer material) same (photoresist mask) same pattern\$3 and (electrode pad terminal)	USPAT; EPO; JPO; DERWEN T; IBM_TD B

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28	BRS	L30	5	29/849 and (interposer substrate carrier) same (conductive metal) adj2 (film layer material) same (photoresist mask) same pattern\$3 and (electrode pad terminal)	USPAT; EPO; JPO; DERWEN T; IBM_TD B
29	BRS	L31	22	29/874 and (interposer substrate carrier) same (conductive metal) adj2 (film layer material) same (photoresist mask) same pattern\$3 and (electrode pad terminal)	USPAT; EPO; JPO; DERWEN T; IBM_TD B
30	BRS	L32	1	29/875 and (interposer substrate carrier) same (conductive metal) adj2 (film layer material) same (photoresist mask) same pattern\$3 and (electrode pad terminal)	USPAT; EPO; JPO; DERWEN T; IBM_TD B
31	BRS	L33	12	29/876 and (interposer substrate carrier) same (conductive metal) adj2 (film layer material) same (photoresist mask) same pattern\$3 and (electrode pad terminal)	USPAT; EPO; JPO; DERWEN T; IBM_TD B
32	BRS	L34	5	29/877 and (interposer substrate carrier) same (conductive metal) adj2 (film layer material) same (photoresist mask) same pattern\$3 and (electrode pad terminal)	USPAT; EPO; JPO; DERWEN T; IBM_TD B

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33	BRS	L35	6	29/878 and (interposer substrate carrier) same (conductive metal) adj2 (film layer material) same (photoresist mask) same pattern\$3 and (electrode pad terminal)	USPAT; EPO; JPO; DERWEN T; IBM_TD B
34	BRS	L36	8	29/879 and (interposer substrate carrier) same (conductive metal) adj2 (film layer material) same (photoresist mask) same pattern\$3 and (electrode pad terminal)	USPAT; EPO; JPO; DERWEN T; IBM_TD B
35	BRS	L37	15	29/884 and (interposer substrate carrier) same (conductive metal) adj2 (film layer material) same (photoresist mask) same pattern\$3 and (electrode pad terminal)	USPAT; EPO; JPO; DERWEN T; IBM_TD B
36	BRS	L38	247	29/\$.ccls. and interposer	USPAT; EPO; JPO; DERWEN T; IBM_TD B
37	BRS	L39	272	"174"/\$.ccls. and interposer	USPAT; EPO; JPO; DERWEN T; IBM_TD B

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38	BRS	L40	54	174/250 and (interposer substrate carrier) same (conductive metal) adj2 (film layer material) same (photoresist mask) same pattern\$3 and (electrode pad terminal)	USPAT; EPO; JPO; DERWEN T; IBM_TD B
39	BRS	L41	80	174/255 and (interposer substrate carrier) same (conductive metal) adj2 (film layer material) same (photoresist mask) same pattern\$3 and (electrode pad terminal)	USPAT; EPO; JPO; DERWEN T; IBM_TD B
40	BRS	L42	76	174/260 and (interposer substrate carrier) same (conductive metal) adj2 (film layer material) same (photoresist mask) same pattern\$3 and (electrode pad terminal)	USPAT; EPO; JPO; DERWEN T; IBM_TD B